In the Claims:

1. (Currently Amended) A method of forming a semiconductor device, the method comprising:

siliciding a source region and a drain region of a first transistor formed on a substrate, the first transistor having a gate electrode with spacers formed alongside the gate electrode;

forming a nitrogen-containing dielectric layer over the gate electrode, the spacers, the source region and the drain region;

removing the nitrogen-containing dielectric layer over the gate electrode; and

siliciding ~~a gate~~ the gate electrode of the first transistor.

2. (Original) The method of claim 1 wherein the step of siliciding the source region and the drain region is performed during the same process steps.

3. (Original) The method of claim 1 wherein the step of siliciding the source region and the drain region includes partially siliciding the gate electrode.

4. (Original) The method of claim 1 wherein the step of siliciding the gate electrode is performed by substantially fully siliciding the gate electrode.

5. (Original) The method of claim 1 wherein the step of siliciding the gate electrode is performed by forming a first metal layer on the gate electrode and annealing.

6. (Original) The method of claim 5 wherein the first metal layer comprises a plurality of layers.

7. (Original) The method of claim 1 wherein the step of siliciding the drain and the source are performed by forming a first metal layer on the source and the drain and annealing, and the

step of siliciding the gate electrode is performed by forming a second metal layer on the gate electrode and annealing.

8. (Original) The method of claim 7 wherein the first metal layer is a metal different from the second metal layer.

9. (Original) The method of claim 7 wherein the second metal layer is a plurality of layers.

10. (Original) The method of claim 7 wherein the step of siliciding the source and the drain includes partially siliciding the gate electrode.

11. (Currently Amended) The method of claim 1 wherein the nitrogen-containing dielectric layer comprises silicon nitride or silicon oxynitride.

12. (Currently Amended) The method of claim 1 further comprising the step of forming a silicon oxide layer over the nitrogen-containing dielectric layer.

13. (Currently Amended) A method of forming a semiconductor device, the method comprising:

siliciding a first source/drain region of a first transistor;

siliciding a second source/drain region of a second transistor;

forming a dielectric layer over the source/drain region and a first gate electrode of the first transistor and the source/drain region and a second gate electrode of the second transistor; ~~and~~

removing the dielectric layer over the first gate electrode and the second gate electrode;

siliciding ~~a first~~ the first gate electrode of the first transistor; and siliciding ~~a second~~ the second gate electrode of the second transistor in a different process step as the step of siliciding the first gate electrode.

14. (Original) The method of claim 13 wherein the step of siliciding the first source/drain region is performed by depositing a first metal layer and annealing.

15. (Original) The method of claim 14 wherein the first metal layer is a plurality of layers.

16. (Original) The method of claim 13 wherein the step of siliciding the first source/drain region and the step of siliciding the second source/drain region is performed with different metals.

17. (Original) The method of claim 13 wherein the step of siliciding the first gate electrode and the step of siliciding the second gate electrode is performed with different metals.

18. (Original) The method of claim 13 wherein the step of siliciding the first source/drain region includes partially siliciding the first gate electrode.

19. (Original) The method of claim 13 wherein the step of siliciding the second source/drain region includes partially siliciding the second gate electrode.

20. (Original) The method of claim 13 wherein the step of siliciding the first gate electrode is performed by substantially fully siliciding the first gate electrode.

21. (Original) The method of claim 13 wherein the step of siliciding the second gate electrode is performed by substantially fully siliciding the second gate electrode.

22. (Original) The method of claim 13 wherein the step of siliciding the first gate electrode is performed by forming a third metal layer on the first gate electrode and annealing.

23. (Original) The method of claim 13 wherein the step of siliciding the second gate electrode is performed by forming a fourth metal layer on the second gate electrode and annealing.

24. (Original) The method of claim 13 wherein the dielectric layer comprises silicon nitride or silicon oxynitride.

25. (Original) The method of claim 13 further comprising the step of forming a silicon oxide layer over the dielectric layer.

26. (Currently Amended) A semiconductor device comprising:

a first transistor; and

a second transistor,

wherein each of the first transistor and the second transistor includes a source, a drain, and a gate electrode, the gate electrode of the first transistor and the gate electrode of the second transistor being silicided with different metals, and wherein a dielectric layer having a thickness less than a thickness of the gate electrode covers at least a portion of the source and the drain of the first and second transistors.

27. (Original) The semiconductor device of claim 26 wherein the gate electrode of the first transistor is substantially fully silicided.

28. (Original) The semiconductor device of claim 26 wherein the gate electrode of the second transistor is substantially fully silicided.

29. (Original) The semiconductor device of claim 26 wherein the source and the drain of the first transistor is silicided with a first metal and the source and the drain of the second transistor are silicided with a second metal.

30. (Original) The semiconductor device of claim 26 wherein the source and the drain of the first transistor is silicided with a metal selected from the group comprising nickel, cobalt, copper, molybdenum, titanium, tantalum, tungsten, erbium, zirconium, platinum, and a combination thereof.

31. (Original) The semiconductor device of claim 26 wherein the gate electrode of the first transistor is silicided with a metal selected from the group comprising nickel, cobalt, copper, molybdenum, titanium, tantalum, tungsten, erbium, zirconium, platinum, and a combination thereof.

32. (Original) The semiconductor device of claim 26 wherein the source and the drain of the second transistor is silicided with a metal selected from the group comprising nickel, cobalt, copper, molybdenum, titanium, tantalum, tungsten, erbium, zirconium, platinum, and a combination thereof.

33. (Original) The semiconductor device of claim 26 wherein the gate electrode of the second transistor are silicided with a metal selected from the group comprising nickel, cobalt, copper, molybdenum, titanium, tantalum, tungsten, erbium, zirconium, platinum, and a combination thereof.

34. (New) A method of forming a semiconductor device, the method comprising:

forming a nitrogen-containing dielectric layer over a gate electrode, a source region, and a drain region of a first transistor formed on a substrate;

removing the nitrogen-containing dielectric layer over the gate electrode;

forming a first metal layer over the gate electrode and the nitrogen-containing dielectric layer, the first metal layer having a non-planar surface; and

siliciding the gate electrode of the first transistor.

35. (New) The method of claim 34 further comprising siliciding the source region and the drain region.

36. (New) The method of claim 35 wherein the siliciding the source region and the drain region includes partially siliciding the gate electrode.

37. (New) The method of claim 34 wherein the siliciding the gate electrode is performed by substantially fully siliciding the gate electrode.

38. (New) The method of claim 34 wherein the siliciding the gate electrode is performed by annealing.

39. (New) The method of claim 34 wherein the first metal layer comprises a plurality of layers.

40. (New) The method of claim 34 wherein the nitrogen-containing dielectric layer comprises silicon nitride or silicon oxynitride.

41. (New) The method of claim 34 further comprising the step of forming a silicon oxide layer over the nitrogen-containing dielectric layer.